TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

## TC74HC4051AP,TC74HC4051AF,TC74HC4051AFT TC74HC4052AP,TC74HC4052AF,TC74HC4052AFT TC74HC4053AP,TC74HC4053AFN,TC74HC4053AFT

TC74HC4051AP/AF/AFT

8-Channel Analog Multiplexer/Demultiplexer

TC74HC4052AP/AF/AFT

Dual 4-Channel Analog Multiplexer/Demultiplexer

TC74HC4053AP/AF/AFN/AFT

Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC74HC4051A/4052A/4053A are high speed CMOS ANALOG MULTIPLEXER/DEMULTIPLEXER fabricated with silicon gate  $C^2MOS$  technology. They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The TC74HC4051A has an 8 channel configuration, the TC74HC4052A has a 4 channel  $\times$  2 configuration and the TC74HC4053A has a 2 channel  $\times$  3 configuration.

The digital signal to the control terminal turns "ON" the corresponding switch of each channel a large amplitude signal ( $V_{\rm CC}-V_{\rm EE}$ ) can then be switched by the small logical amplitude ( $V_{\rm CC}-G_{\rm ND}$ ) control signal.

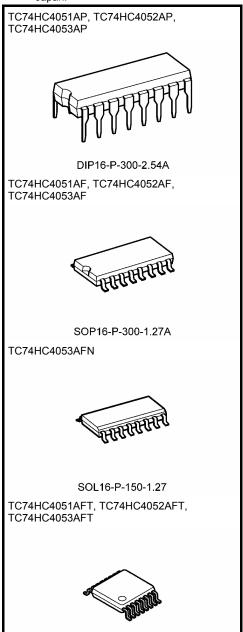
For example, in the case of  $V_{\rm CC}=5$  V, GND = 0 V,  $V_{\rm EE}=-5$  V, signals between –5 V and +5 V can be switched from the logical circuit with a single power supply of 5 V. As the ON-resistance of each switch is low, they can be connected to circuits with low input impedance.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### **Features**

- High speed:  $t_{pd} = 15 \text{ ns (typ.)}$  at  $V_{CC} = 5 \text{ V}$ ,  $V_{EE} = 0 \text{ V}$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max)}$  at  $T_a = 25^{\circ}C$
- High noise immunity: VNIH = VNIL = 28% VCC (min)
- Low ON resistance:  $R_{ON} = 50 \Omega$  (typ.) at  $V_{CC} V_{EE} = 9 V$
- High noise immunity: THD = 0.02% (typ.) at  $V_{CC} V_{EE} = 9 \text{ V}$
- Pin and function compatible with 4051/4052/4053B

Note: xxxFN (JEDEC SOP) is not available in Japan.



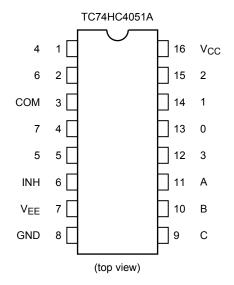
Weight

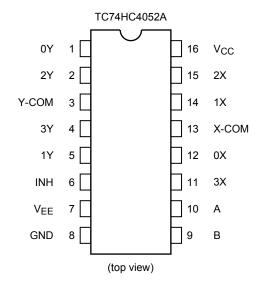
DIP16-P-300-2.54A : 1.00 g (typ.) SOP16-P-300-1.27A : 0.18 g (typ.) SOL16-P-150-1.27 : 0.13 g (typ.) TSSOP16-P-0044-0.65A : 0.06 g (typ.)

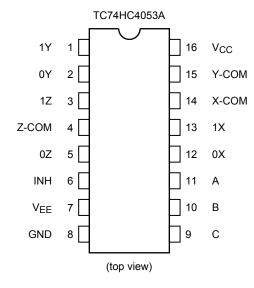
TSSOP16-P-0044-0.65A



## **Pin Assignment**



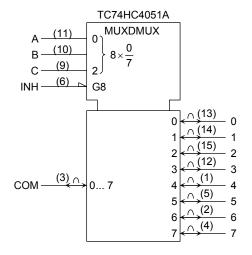


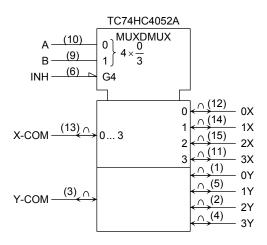


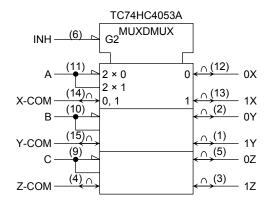
2



## **IEC Logic Symbol**







#### **Truth Table**

	Contro	I Inputs		"ON" Channel					
Inhibit	C*	В	Α	HC4051A	HC4052A	HC4053A			
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z			
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z			
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z			
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z			
L	Η	L	L	4	_	0X, 0Y, 1Z			
L	Н	L	Н	5	_	1X, 0Y, 1Z			
L	Н	Н	L	6	_	0X, 1Y, 1Z			
L	Н	Н	Н	7	_	1X, 1Y, 1Z			
Н	Х	Х	Х	None	None	None			

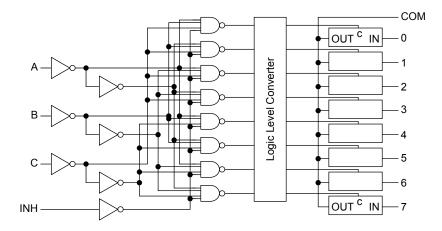
X: Don't care

\*: Except HC4052A

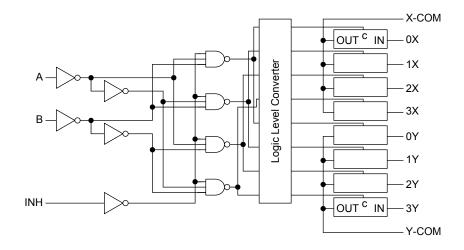
3

## **System Diagram**

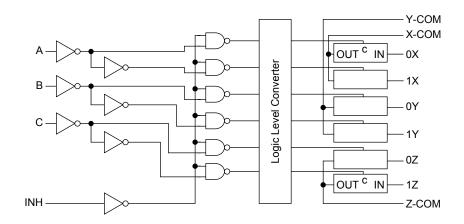
### TC74HC4051A



#### TC74HC4052A



#### TC74HC4053A



4



#### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	–0.5 to 7	V
Supply voltage range	V <sub>CC</sub> -V <sub>EE</sub>	−0.5 to 13	V
Control input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> – 0.5 to V <sub>CC</sub> + 0.5	V
Control input diode current	I <sub>ICK</sub>	±20	mA
I/O diode current	lok	±20	mA
Switch through current	ΙΤ	±25	mA
DC V <sub>CC</sub> or ground current	Icc	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP, TSSOP)	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	2 to 6	V
Supply voltage range	V <sub>EE</sub>	-6 to 0	V
Supply voltage range	V <sub>CC</sub> -V <sub>EE</sub>	2 to 12	V
Control input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
		0 to 1000 (V <sub>CC</sub> = 2.0 V)	
Control input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0 to 500 (V <sub>CC</sub> = 4.5 V)	ns
		0 to 400 (V <sub>CC</sub> = 6.0 V)	

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused control inputs must be tied to either VCC or GND.

5 2007-10-01



## **Electrical Characteristics**

### **DC Characteristics**

Characteristics	Symbol	Test Condition			-	Га = 25°(		Ta = -40 to 85°C		Unit
	- ,		V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
				2.0	1.50	_	_	1.50	_	٧
High-level control input voltage	$V_{IHC}$	_		4.5	3.15	_	_	3.15	_	
I mpar remage				6.0	4.20	_	_	4.20	_	
				2.0	_	_	0.50	_	0.50	
Low-level control input voltage	$V_{ILC}$	_		4.5	_	_	1.35	_	1.35	V
			-	6.0			1.80		1.80	
		$V_{IN} = V_{ILC}$ or $V_{IHC}$	GND	4.5		85	180	_	225	
		$V_{I/O} = V_{CC}$ to $V_{EE}$	-4.5	4.5	_	55	120	_	150	
	R <sub>ON</sub>	$I_{I/O} \leq 2 \ mA$	-6.0	6.0		50	100		125	
ON resistance		$V_{IN} = V_{ILC}$ or $V_{IHC}$ $V_{I/O} = V_{CC}$ or $V_{EE}$	GND	2.0		150	_	_	_	Ω
			GND	4.5	_	70	150	_	190	
		I <sub>I/O</sub> ≤ 2 mA	-4.5	4.5	_	50	100	_	125	
		1 /O ≤ 2 111A	-6.0	6.0		45	80	_	100	
Difference of ON	ΔR <sub>ON</sub>	$V_{IN} = V_{ILC}$ or $V_{IHC}$	GND	4.5	_	10	30	_	35	Ω
resistance between		$V_{I/O} = V_{CC}$ to $V_{EE}$	-4.5	4.5	_	5	12	_	15	
switches		$I_{I/O} \leq 2 \ mA$	-6.0	6.0		5	10		12	
Input/output leakage		$V_{OS} = V_{CC}$ or GND	GND	6.0			±60		±600	
current	l <sub>OFF</sub>	$V_{IS} = GND \text{ or } V_{CC}$	-6.0	6.0			±100	_	±1000	nA
(switch off)		$V_{IN} = V_{ILC}$ or $V_{IHC}$	-0.0	0.0			±100		±1000	
Switch input leakage	_	V <sub>OS</sub> = V <sub>CC</sub> or GND	GND	6.0	_	_	±60	_	±600	
current (switch on)	I <sub>IZ</sub>	V <sub>IN</sub> = V <sub>ILC</sub> or V <sub>IHC</sub>	-6.0	6.0	_	_	±100	_	±1000	nA
Control input current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND	GND	6.0			±0.1		±1.0	μА
	IN	AIM - ACC OL GIAD	GND	6.0			4.0		40.0	μΑ
Quiescent supply current	Icc	$V_{IN} = V_{CC}$ or GND	-6.0	6.0			8.0	_		μΑ
			<b>−</b> 0.U	0.0	_		ŏ.U	_	80.0	

6 2007-10-01



AC Characteristics ( $C_L = 50 \text{ pF}$ , input:  $t_r = t_f = 6 \text{ ns}$ , GND = 0 V)

Charactaristics	Symbol		Test Cor	Test Condition		-	Ta = 25°0	<b>C</b>	Ta = -40 to 85°C		Unit
Characteristics	Symbol			V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
				GND	2.0	_	25	60	_	75	
Phase difference		A II 4:		GND	4.5	_	6	12	_	15	
between input and output	ΦΙ/Ο	All types		GND	6.0	_	5	10	_	13	ns
				-4.5	4.5		4	_	_	_	
				GND	2.0	_	64	225	_	280	
		4051	(Note 1)	GND	4.5	_	18	45	_	56	
		4031	(Note 1)	GND	6.0	_	15	38	_	48	
				-4.5	4.5		18	_	_	_	
				GND	2.0	_	64	225	_	280	
Output enable time	t <sub>pZL</sub>	4052	(Note 1)	GND	4.5	_	18	45	_	56	ns
Cutput chable time	t <sub>pZH</sub>	7002	(14010-1)	GND	6.0	_	15	38	_	48	110
				-4.5	4.5		18	_	_	_	
				GND	2.0	_	50	225	_	280	
		4053	(Note 1)	GND	4.5	_	14	45	_	56	
				GND	6.0	_	12	38	_	48	
				-4.5	4.5		14	_	_	_	
			(Note 1)	GND	2.0	_	100	250	_	315	
		4051		GND	4.5	_	33	50	_	63	ns
				GND	6.0	_	28	43	_	54	
				-4.5	4.5		29	_	_	_	
	<sup>t</sup> pLZ	4052	(Note 1)	GND	2.0	_	100	250		315	
Output disable time				GND	4.5	_	33	50	_	63	
	t <sub>pHZ</sub>			GND	6.0	_	28	43	_	54	
				-4.5	4.5		29	_	_	_	
				GND	2.0	_	95	225	_	280	
		4053	(Note 1)	GND	4.5	_	30	45	_	56	
				GND	6.0	_	26	38	_	48	
				-4.5	4.5		26		_	_	
Control input capacitance	C <sub>IN</sub>	All types		_	_	_	5	10	_	10	pF
COMMON terminal		4051				_	36	70	_	70	
capacitance	C <sub>IS</sub>	4052		-5.0	5.0	_	19	40		40	pF
		4053				_	11	20	_	20	
SWITCH terminal		4051				_	7	15		15	
capacitance	C <sub>OS</sub>	4052		-5.0	5.0	_	7	15	_	15	pF
		4053				_	7	15	_	15	
Feedthrough		4051				_	0.95	2	_	2	
capacitance	C <sub>IOS</sub>	4052		-5.0	5.0	_	0.85	2	_	2	pF
		4053				_	0.75	2	_	2	
Power dissipation		4051				_	70	_	_	_	
capacitance	C <sub>PD</sub>	4052	(Note 2)	GND	5.0	_	71	_	_	_	pF
•		4053				_	67	_	_	_	

Note 1:  $R_L = 1 k\Omega$ 

Note 2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

7

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 



## Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note 1)

		Test Condition						
Characteristics	Symbol						Тур.	Unit
Sine wave distortion		$R_L = 10 \text{ k}\Omega,$	$V_{IN} = $	4.0 V <sub>p-p</sub>	-2.25	2.25	0.025	
(T.H.D)		C <sub>L</sub> = 50 pF	$V_{IN}=8.0\ V_{p\text{-}p}$		-4.5	4.5	0.020	%
(1.11.0)		f <sub>IN</sub> = 1 kHz	V <sub>IN</sub> =	11.0 V <sub>p-p</sub>	-6.0	6.0	0.018	
			All	(Note 2)			120	
			4051	(Note 3)	-2.25	2.25	45	
			4052		-2.23	2.23	70	
		Adjust for valtage to obtain	4053				95	
		Adjust f <sub>IN</sub> voltage to obtain 0dBm at V <sub>OS</sub>	All	(Note 2)	-4.5	4.5	190	MHz
Frequency response	f <sub>max</sub>	Increase $f_{IN}$ frequency until dB meter reads $-3$ dB $R_L = 50 \Omega$ , $C_L = 10 pF$ $f_{IN} = 1 \text{ MHz}$ , sine wave	4051	(Note 3)			70	
(switch on)			4052				110	
			4053				150	
			All	(Note 2)		6.0	200	
			4051	(Note 3)			85	
			4052				140	
			4053				190	
			v is centered at (V <sub>CC</sub> – V <sub>EE</sub> )/2					
Feed through attenuation		djust input for 0dBm $R_L = 600 \ \Omega, \ C_L = 50 \ pF$			-4.5	2.25 4.5 6.0	-50	dB
(switch off)					-6.0		-50	
		f <sub>IN</sub> = 1 MHz, sine wave						
Crosstalk		$R_{I} = 600 \Omega, C_{I} = 50 pF$			-2.25	2.25	60	
(control input to signal output)		f <sub>IN</sub> = 1 MHz, square wave (	$(t_r = t_f =$	6 ns)	-4.5	4.5	140	mV
				-6.0	6.0	200		
Crosstalk		Adjust V <sub>IN</sub> to obtain 0dBm at	input		-2.25 -4.5	2.25 4.5	-50 -50	
(between any switches)			$R_L = 600 \Omega, C_L = 50 pF$				-50 	dB
		f <sub>IN</sub> = 1 MHz, sine wave					-50	

8

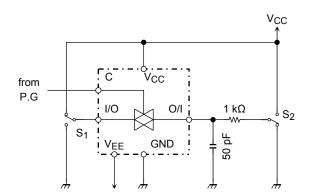
Note 1: These characteristics are determined by design of devices.

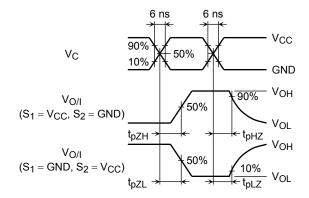
Note 2: Input COMMON terminal, and measured at SWITCH terminal.

Note 3: Input SWITCH terminal, and measured at COMMON terminal.

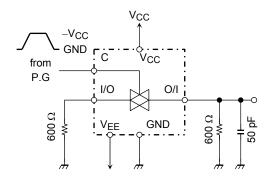
### **Switching Characteristics Test Circuits**

# $1. \quad t_{pLZ},\, t_{pHZ},\, t_{pZL},\, t_{pZH}$

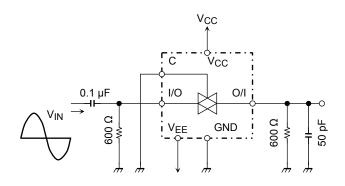




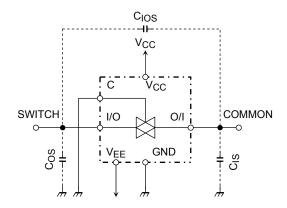
### 2. Cross Talk (control input-switch output) $f_{IN} = 1$ MHz duty = 50% $t_r = t_f = 6$ ns



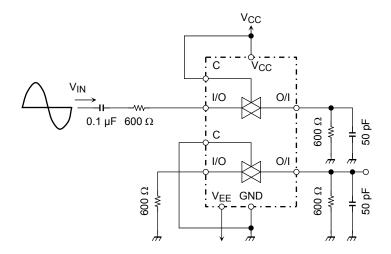
### 3. Feedthrough Attenuation



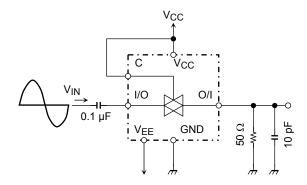
#### 4. CIOS, CIS, COS



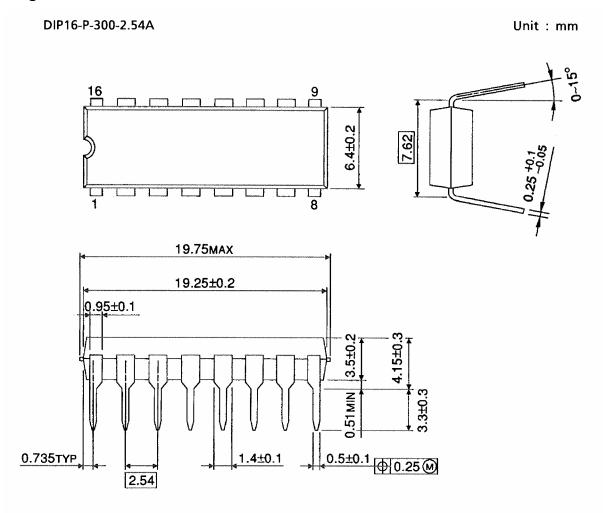
### 5. Cross Talk (between any two switches)



### 6. Frequency Response (switch on)



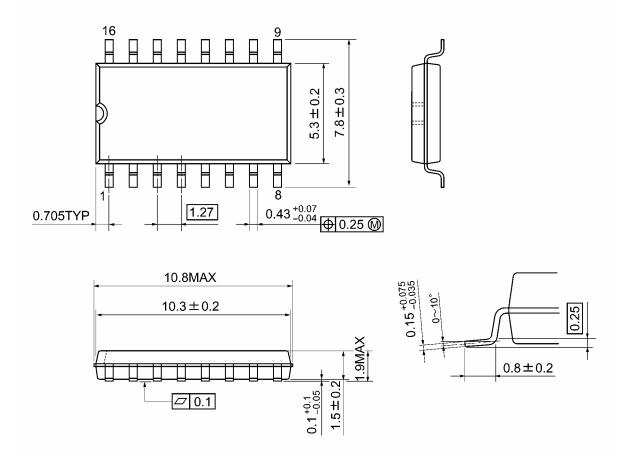
## **Package Dimensions**



Weight: 1.00 g (typ.)

## **Package Dimensions**

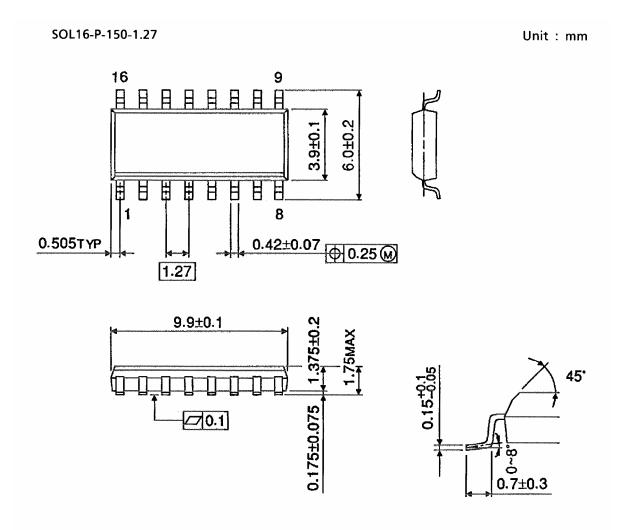
SOP16-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)



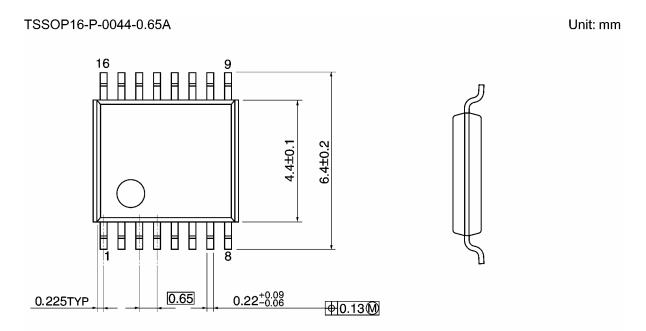
## **Package Dimensions (Note)**

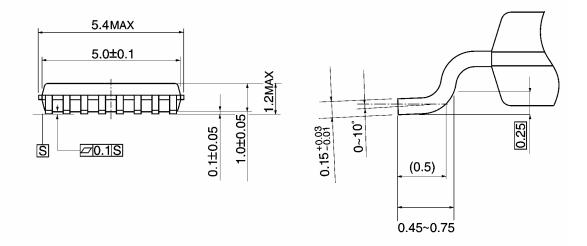


Note: This package is not available in Japan.

Weight: 0.13 g (typ.)

## **Package Dimensions**





Weight: 0.06 g (typ.)

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which
  manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
  may result from its use. No license is granted by implication or otherwise under any patents or other rights of
  TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
  compatibility. Please use these products in this document in compliance with all applicable laws and regulations
  that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
  occurring as a result of noncompliance with applicable laws and regulations.